

Part Number

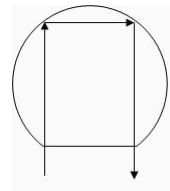
Customer

Category	Parameter	Specification	Measurement Method	
OverallWafer	1.0	Diameter	150.00 +/- 0.30 mm	
	2.0	Primary Flat Orientation	{110} +/- 1 degree	Wafer Vendor
	3.0	Primary Flat Length	47.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	None	
	5.0	Overall Thickness	681.00 +/- 6.00 μ m	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00 μ m	Guaranteed by Process
	7.0	Bow	<80.00 μ m	ADE to ASTM F534, 20%
	8.0	Warp	<80.00 μ m	ADE to ASTM F657, 20%
	9.0	Edge Chips	zero as per semi standard (>0.25mm X 0.25mm)	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	7mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 1 degree	Wafer Vendor
	13.0	Handle Thickness	600.00 +/- 5.00 μ m	ADE, 100%
	14.0	Handle Doping Type	N	Wafer Vendor
	15.0	Handle Dopant	Phosphorous	Wafer Vendor
	16.0	Handle Resistivity	1 - 10 Ohmcm	Wafer Vendor
	17.0	Backside Finish	Lapped and Etched	Wafer Vendor
BuriedOxide	18.0	Oxide Type	Thermal	
	19.0	Oxide Thickness	20,000.00 +/- 1,000.00 A	Nanospec centre point, 4%
	20.0	Oxide formed on	Device Wafer	
DeviceSilicon	21.0	Device Growth Method	Low Oi CZ	Wafer Vendor
	22.0	Oxygen Concentration	<14.00ppma	New ASTM
	23.0	Device Orientation	{100} +/- 1 degree	Wafer Vendor
	24.0	Nominal Thickness	78.00 +/- 2.00 μ m	FTIR, 100% 9-Pt (note3)
	25.0	Distance to device silicon edge from wafer edge	< 5mm	Typical by Process, no edge grind.
	26.0	Edge Removal Depth in Handle	<100 μ m	Typical by process
	27.0	Device Doping Type	N	Wafer Vendor
	28.0	Device Dopant	Phosphorous	Wafer Vendor
	29.0	Device Resistivity	1 - 3 Ohm-cm	Wafer Vendor
	33.0	Voids	0	Bright Light, 100% (note2)
	34.0	Scratches	<25mm total length	Bright Light, 100% (note2)
	35.0	Haze	none	Bright Light, 100% (note2)

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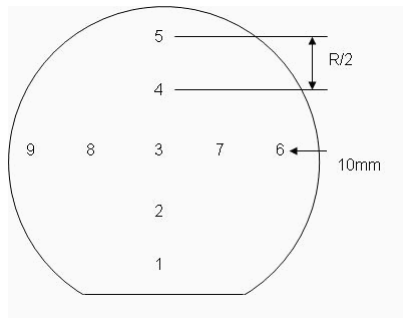
Shipping Details	Wafer per box :	Max 25
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information